

RF AMPLIFIER

MODEL *TR9794*

Available as: TR9794, 4 Pin TO-8B
 RN9794, 4 Pin Surface Mount (SM19)
 BR9794, Connectorized Housing (H2)

Preliminary

Features

- GaAs FET Amplifier; Medium Gain: 13.5 dB Typ.
- High Output Power: +26.5 dBm Typical
- Operating Temp. - 55 °C to +85 °C
- Environmental Screening Available

Specifications

CHARACTERISTIC	TYPICAL Ta= 25 °C	MIN/MAX Ta = -55 °C to +85 °C
Frequency	600 - 1100 MHz	600 - 1100 MHz
Gain (dB)	13.5	12.5 Min.
Power @ 1 dB Comp. (dBm)	+26.5	+25.0 Min.
Reverse Isolation (dB)	-15	-14 Max.
VSWR In	<1.75:1	2.0:1 Max.
Out	<1.50:1	2.0:1 Max.
Noise figure (dB)	<3.0	3.5 Max.
Power Vdc	+15	+15
mA	185	195 Max.

Note: Care should always be taken to effectively ground the case of each unit.

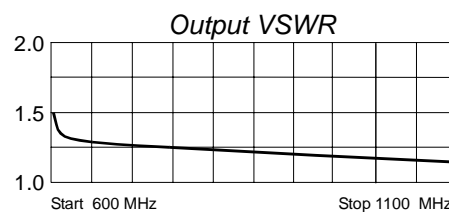
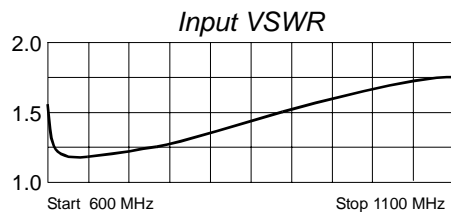
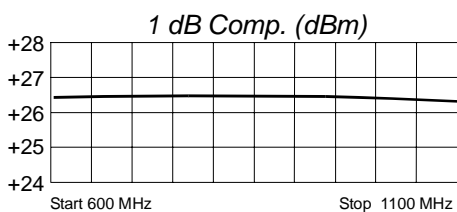
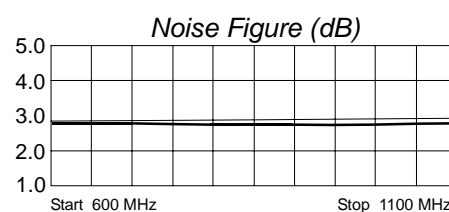
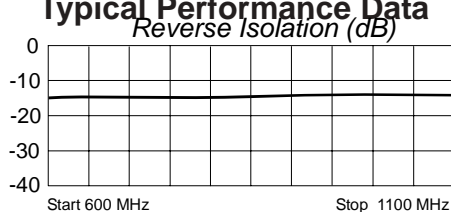
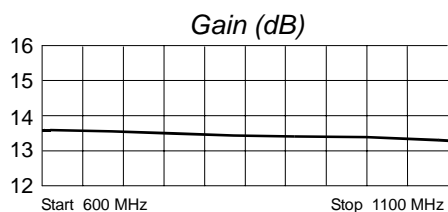
Typical Intermodulation Performance at 25 ° C

Second Order Harmonic Intercept Point +61 dBm (Typ.)
 Second Order Two Tone Intercept Point +55 dBm (Typ.)
 Third Order Two Tone Intercept Point +40 dBm (Typ.)

Maximum Ratings

Ambient Operating Temperature -55°C to + 100 °C
 Storage Temperature -62°C to + 125 °C
 Case Temperature + 125 °C
 DC Voltage + 17 Volts
 Continuous RF Input Power + 17 dBm
 Short Term RF Input Power 150 Milliwatts (1 Minute Max.)
 Maximum Peak Power 0.3 Watt (3 µsec Max.)

Typical Performance Data



Legend ——— + 25 °C - - - - + 85 °C - - - - - - - - - -55 °C

